FA	IRCHI	LD				March 1999	
	6324L arated Lo	ad Switch					
-	-			Features			
	I Description						
These Integrated Load Switches are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage high side load switch application where low conduction loss and ease of driving			ology. This very high o minimize on-state performance. These Itage high side load	 V_{DROP}=0.2V @ V_{IN}=12V, I_L=1A, V_{ONOFF}=1.5 to 8V V_{DROP}=0.3V @ V_{IN}=5V, I_L=1A, V_{ONOFF}=1.5 to 8V. High density cell design for extremely low on-resistance. V_{ONOFF} Zener protection for ESD ruggedness. >6KV Human Body Model. 			
are need	ed.			■ SuperSOT TM -6	i package design using co ectrical capabilities.	pper lead frame for super	
I	÷						
SOT-	-23	SuperSOT [™] -6	SuperSOT [™] -8	SO-8	SOT-223	SOIC-16	
		RE	ON/OFF 5 		Vout,C1 IN • ON/OFF	Votor Votor OUT	
Supe	_{pin} 1 ¹ erSOT ™_6		R1,C1 6		Vout,C1		
\bsolu	erSOT ™6 <u>ute Operatii</u>		R1,C1 6		Vout,C1	· · · · · · · · · · · · · · · · · · ·	
L bsolu ymbol	erSOT [™] 6 ute Operatii Parameter	ng Range ा₄	R1,C1 6		Vout,C1		
\bsolu ymbol	erSOT ™6 ute Operatiu Parameter Input Voltage	n g Range T _A . Range	R1,C1 6		Vout,C1 ON/OFF R2 FDC6324L		
Absolu ymbol IN ON/OFF	erSOT ™6 ute Operatii Parameter Input Voltage ON/OFF Volta	n g Range T _A : Range Ige Range	R1,C1 6 See A		Vout,C1 N/OFF R2 FDC6324L 3 - 20		
Absolu ymbol IN ON/OFF	erSOT ™6 ute Operatii Parameter Input Voltage ON/OFF Volta	n g Range T _A . Range	= 25°C unless otherwise noted	pplication Circuit	Vout,C1 N/OFF R2 FDC6324L 3 - 20 1.5 - 8	Units V V V	
NDSOLU ymbol IN ON/OFF	erSOT ™6 ute Operatiu Parameter Input Voltage ON/OFF Volta Load Current	ng Range _{T_A} : Range Ige Range @ V _{DROP} =0.5V - Co	= 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3	pplication Circuit	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5	Units	
Lbsolu ymbol IN ONVOFF	erSOT ™6 ute Operatin Parameter Input Voltage ON/OFF Volta Load Current Maximum Pow	n g Range T _A : Range Ige Range	= 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3 (Note 2a)	pplication Circuit	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8 1.5	Units V V A	
bsolu ymbol N ONVOFF	erSOT ™6 ute Operation Parameter Input Voltage ON/OFF Volta Load Current Maximum Pow Operating and	ng Range Range Ige Range @ V _{DROP} =0.5V - Co ver Dissipation Storage Temperatu Discharge Rating MII	= 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3 (Note 2a)	pplication Circuit	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7	Units Units V V V V W W	
Absolu ymbol IN ON/OFF L D J, T _{STG} SD	erSOT ™6 ute Operatin Parameter Input Voltage ON/OFF Volta Load Current Maximum Pow Operating and Electrostatic D	ng Range Range Ige Range @ V _{DROP} =0.5V - Co ver Dissipation Storage Temperatu Discharge Rating MII 15000hm)	= 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3 (Note 2a) re Range	pplication Circuit	Vout,C1 R2	Image: Constraint of the second sec	
Absolu symbol in onvoff L J J, T _{STG} SD	erSOT [™] 6 ute Operatin Parameter Input Voltage ON/OFF Volta Load Current Maximum Pow Operating and Electrostatic D Model (100pf// L CHARACTER	ng Range Range Ige Range @ V _{DROP} =0.5V - Co ver Dissipation Storage Temperatu Discharge Rating MII 15000hm)	= 25°C unless otherwise noted = 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3 (Note 2a) re Range L-STD-883D Human Body	pplication Circuit	Vout,C1 R2	Image: Constraint of the second sec	

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Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS		•			-
I _{FL}	Forward Leakage Current	V _{IN} = 20 V, V _{ON/OFF} = 0 V			1	μA
I _{RL}	Reverse Leakage Current	V _{IN} = -20 V, V _{ON/OFF} = 0 V			-1	μΑ
ON CHAR	ACTERISTICS (Note 3)	· ·				
V _{IN}	Input Voltage		3		20	V
V _{ON/OFF}	On/Off Voltage		1.5		8	V
V _{DROP}	Conduction Voltage Drop @ 1A	V _{IN} = 10 V, V _{ON/OFF} = 3.3V		0.135	0.2	V
		V _{IN} = 5 V, V _{ONOFF} = 3.3 V		0.215	0.3	1
IL	Load Current	V _{DROP} = 0.2 V, V _{IN} = 10 V, V _{ON/OFF} = 3.3 V	1			Α
		V _{DROP} = 0.3 V, V _{IN} = 5 V, V _{ON/OFF} = 3.3 V	1			1

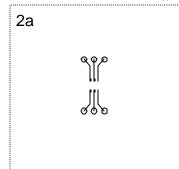
Notes:

1. V_{IN} =20V, V_{ONOFF} =8V, V_{DROP} =0.5V, T_A =25°C

2. R_{BA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BA} is guaranteed by design while $\mathrm{R}_{_{\theta CA}}$ is determined by the user's board design.

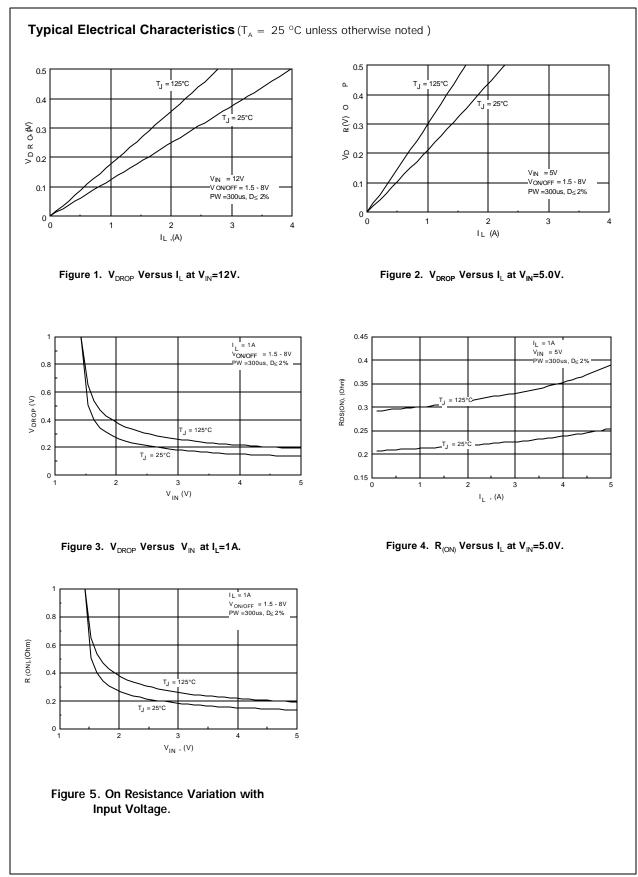
 $P_{D}(t) = \frac{T_{r}T_{s}}{R_{0,j}t} = \frac{T_{r}-T_{s}}{R_{0,j}tR_{0,c}(t)} = I_{D}^{2}(t) \times R_{DQON(\mathcal{G}_{J})}$ Typical R_{0.4} for single device operation using the board layouts shown below on FR-4 PCB in astill air environment

a. 180°C/W when mounted on a 2oz minimum copper pad.

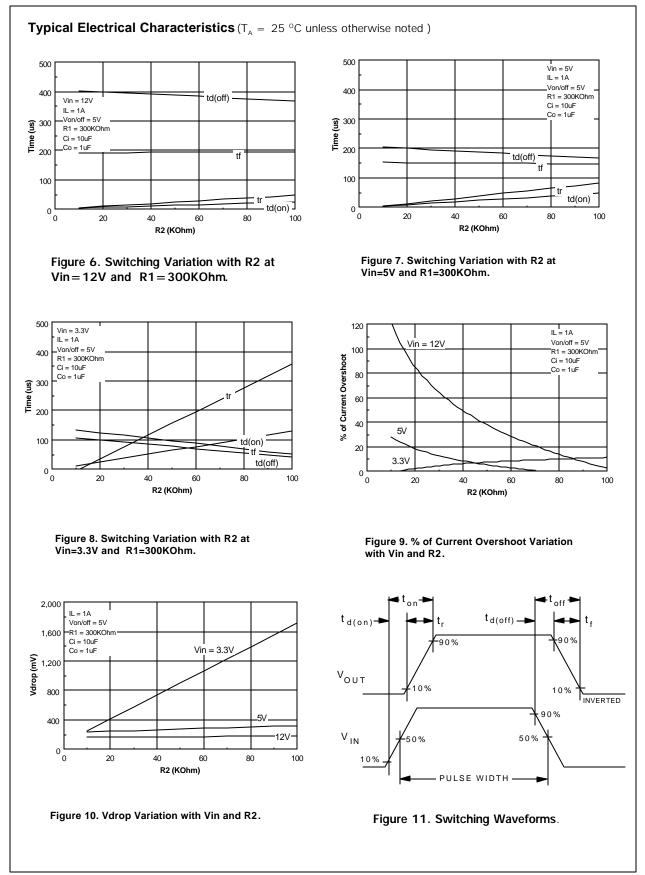


Scale 1 : 1 on letter size paper

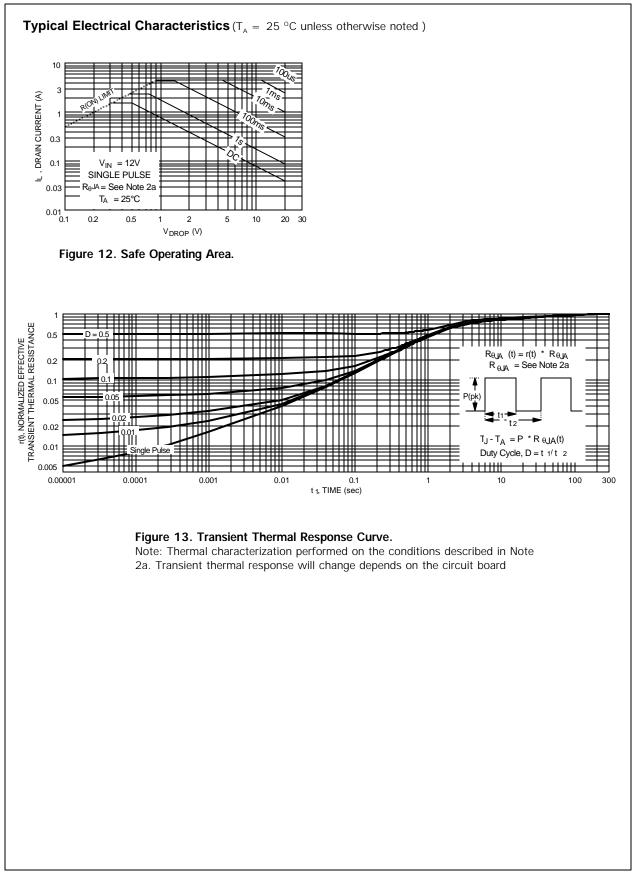
3. Pulse Test: Pulse Width < 300µs, Duty Cycle< 2.0%



FDC6324L Rev.D

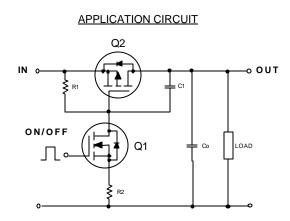


FDC6324L Rev. D



FDC6324L Rev. D

FDC6324L Load Switch Application



General Description

This device is particularly suited for computer peripheral switching applications where 20V input and 1A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N-Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N-Channel device the driving stage is simplified.

Component Values

R1	Typical 10k - $1M\Omega$	
R2	Typical 0-10kΩ	(optional)
C1	Typical 1000pF	(optional)

Design Notes

- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in the case the output capacitance Co is small.
- $R2 \leq$ should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation

 $I_{BIAS _LOSS} = \frac{Vin}{R1 \pm R2}$ when the switch is ON. $I_{BIAS _LOSS}$ can be minimized by large R1.

• R2 and C_{RSS} of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C1 can be added externally to slow down the turn on.

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TinyLogic™ UHC™ VCX™

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